

INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL MOS TYPE

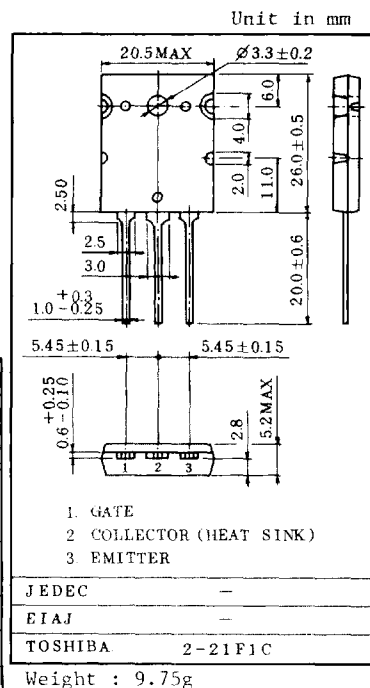
GT60M101

HIGH POWER SWITCHING APPLICATIONS.

- High Input Impedance
- High Speed : $t_f=0.7\mu s(\text{Max.})$
- Low Saturation Voltage : $V_{CE}(\text{sat})=4.0V(\text{Max.})$
- Enhancement-Mode

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	900	V
Gate-Emitter Voltage	V_{GES}	± 25	V
Collector Current	DC	I_C	A
	lms	I_{CP}	
Collector Power Dissipation ($T_c=25^\circ\text{C}$)	P_C	200	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ\text{C}$
Screw Torque	-	8	$\text{kg}\cdot\text{cm}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GES}	$V_{GE}=\pm 25V, V_{CE}=0$	-	-	± 500	nA
Collector Cut-off Current	I_{CES}	$V_{CE}=900V, V_{GE}=0$	-	-	1.0	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=2mA, V_{GE}=0$	900	-	-	V
Gate-Emitter Cut-off Voltage	$V_{GE}(\text{off})$	$I_C=60mA, V_{CE}=5V$	2.0	3.5	5.0	V
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})(1)$	$I_C=10A, V_{GE}=15V$	-	-	2.0	V
	$V_{CE}(\text{sat})(2)$	$I_C=60A, V_{GE}=15V$	-	2.7	4.0	
Input Capacitance	C_{ies}	$V_{CE}=10V, V_{GE}=0, f=1\text{MHz}$	-	2300	-	pF
Switching Time	Rise Time		-	0.3	1.0	μs
	Turn-on Time		-	0.4	1.0	
	Fall Time		-	0.4	0.7	
	Turn-off Time		-	1.0	1.5	
Thermal Resistance	$R_{th(j-c)}$	-	-	-	0.625	$^\circ\text{C/W}$

